

10/811729

ATTORNEY DOCKET No. 91-C-134D2 (STMI01-00098)
DIVISIONAL PATENT

AMENDMENTS TO THE SPECIFICATION

On page 2 at lines 1-2 of the specification, please replace the title with the following:

METHOD OF FORMING ASYMMETRICAL POLYSILICON THIN FILM TRANSISTOR

On page 2 at line 3 of the specification, prior to FIELD OF THE INVENTION, please insert the following:

This application claims priority as a division of prior U.S. Application Serial No.

08/193,725 filed on February 9, 1994, ^{Pat 6,753,574}